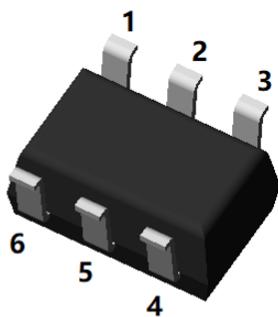
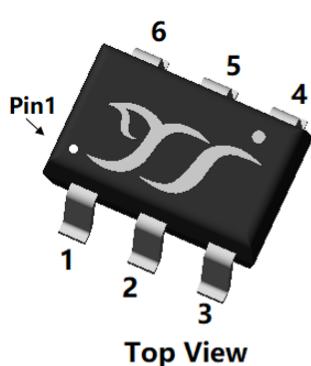
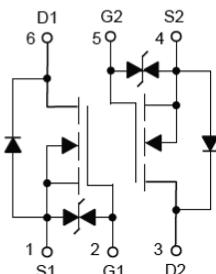


N-Channel and N-Channel Complementary MOSFET

**SOT-363**

Product Summary

- V_{DS} 60V
- I_D 0.3A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) $<2.0\Omega$
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) $<2.5\Omega$
- $R_{DS(ON)}$ (at $V_{GS}=2.5V$) $<3.5\Omega$
- ESD Protected Up to 2kV (HBM)

General Description

- Trench Power MV MOSFET technology
- Voltage controlled small signal switch
- Low input Capacitance
- Fast Switching Speed
- Low Input / Output Leakage
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Part no. with suffix "Q" means AEC-Q101 qualified
- Halogen Free

Applications

- Battery operated systems
- Solid-state relays
- Direct logic-level interface: TTL/CMOS

■ Limiting Values

Parameter	Conditions		Symbol	Min	Max	Unit
Drain-source Voltage			V_{DS}	-	60	V
Gate-source Voltage			V_{GS}	-20	20	
Continuous Drain Current (Note 1,2)	Steady-State	$T_A=25^\circ C, V_{GS}=10V$	I_D	-	0.3	A
		$T_A=100^\circ C, V_{GS}=10V$		-	0.2	
Pulsed Drain Current	$T_A=25^\circ C, t_p \leq 10\mu s$		I_{DM}	-	1.85	
Maximum Body-Diode Continuous Current	$T_A=25^\circ C$		I_S		0.3	
Total Power Dissipation (Note 1,2)	Steady-State	$T_A=25^\circ C$	P_D	-	0.36	W
		$T_A=100^\circ C$		-	0.17	
Junction and Storage Temperature Range			T_J, T_{STG}	-55	175	°C

■ Thermal Resistance

Parameter	Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient (Note 2)	$R_{\theta JA}$	-	410	°C/W

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
2N7002DWKFHQ	F2	72KF	3000	30000	120000	7" reel



■ Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A, T_j=25^\circ C$	60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V, T_j=25^\circ C$	-	-	1	μA
		$V_{DS}=60V, V_{GS}=0V, T_j=150^\circ C$	-	-	100	
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V, T_j=25^\circ C$	-	-	± 10	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A, T_j=25^\circ C$	0.55	0.85	1.15	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=0.3A, T_j=25^\circ C$	-	0.9	2.0	Ω
		$V_{GS}=4.5V, I_D=0.2A, T_j=25^\circ C$	-	1.0	2.5	
		$V_{GS}=2.5V, I_D=0.1A, T_j=25^\circ C$		1.2	3.5	
Diode Forward Voltage	V_{SD}	$I_S=0.3A, V_{GS}=0V, T_j=25^\circ C$	-	0.84	1.2	V
Gate Resistance	R_G	$f=1MHz, T_j=25^\circ C$	-	100	-	Ω
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{DS}=30V, V_{GS}=0V, f=1MHz, T_j=25^\circ C$	-	23	-	pF
Output Capacitance	C_{oss}		-	4.5	-	
Reverse Transfer Capacitance	C_{rss}		-	1.7	-	
Switching Parameters						
Total Gate Charge	Q_g	$V_{GS}=10V, V_{DS}=30V, I_D=0.3A, T_j=25^\circ C$	-	1.1	-	nC
Gate-Source Charge	Q_{gs}		-	0.07	-	
Gate-Drain Charge	Q_{gd}		-	0.15	-	
Reverse Recovery Charge	Q_{rr}	$I_F=0.3A, di/dt=100A/\mu s, V_{GS}=0V, V_R=30V, T_j=25^\circ C$	-	10.7	-	nC
Reverse Recovery Time	t_{rr}		-	32.6	-	
Turn-on Delay Time	$t_{D(on)}$		-	2.9	-	
Turn-on Rise Time	t_r		-	2.6	-	
Turn-off Delay Time	$t_{D(off)}$	$V_{GS}=10V, V_{DS}=30V, I_D=0.3A, R_{GEN}=3\Omega, T_j=25^\circ C$	-	15.9	-	ns
Turn-off Fall Time	t_f		-	43.3	-	

Note:

- The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
- The value of $R_{\theta JA}$ is measured with the device mounted on the 40mm*40mm*1.1mm single layer FR-4 PCB board with 1 in² pad of 2oz. Copper, in the still air environment with $T_A=25^\circ C$. The maximum allowed junction temperature of 175°C. The value in any given application depends on the user's specific board design.
- Thermal resistance from junction to soldering point (on the exposed drain pad).



2N7002DWKFHQ

■ Typical Electrical and Thermal Characteristics Diagrams

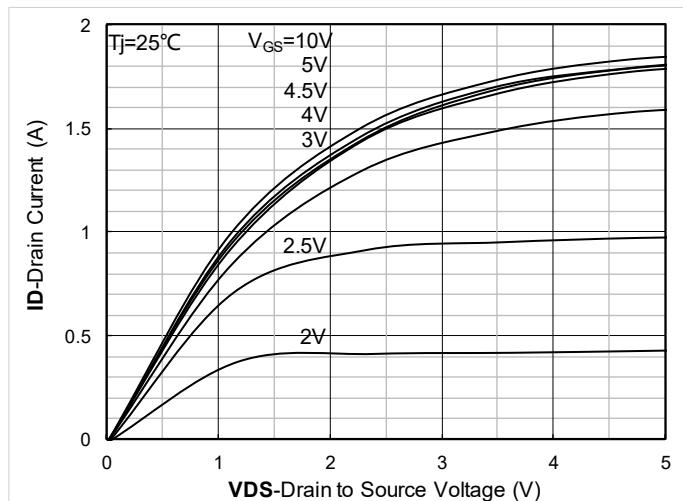


Figure 1. Output Characteristics; typical values

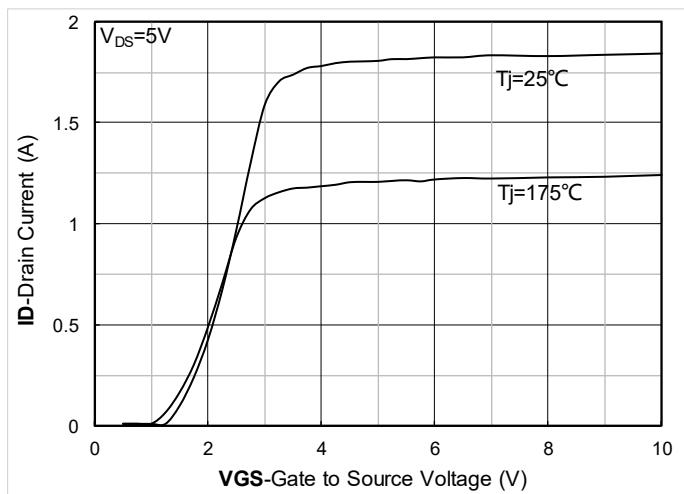


Figure 2. Transfer Characteristics; typical values

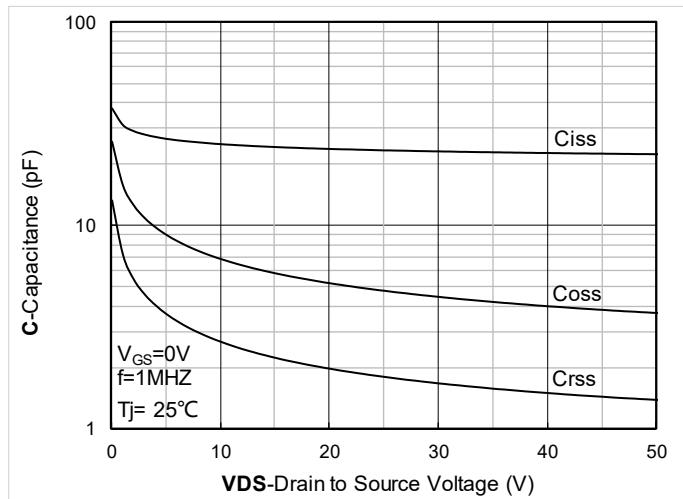


Figure 3. Capacitance Characteristics; typical values

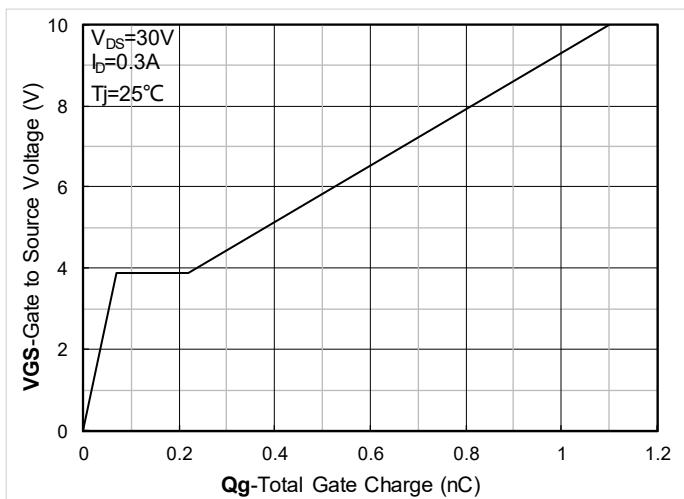


Figure 4. Gate Charge; typical values

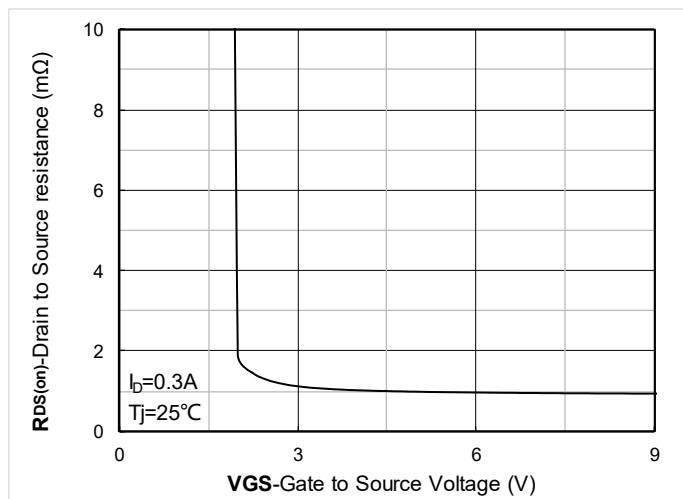


Figure 5. On-Resistance vs. Gate to Source Voltage; typical values

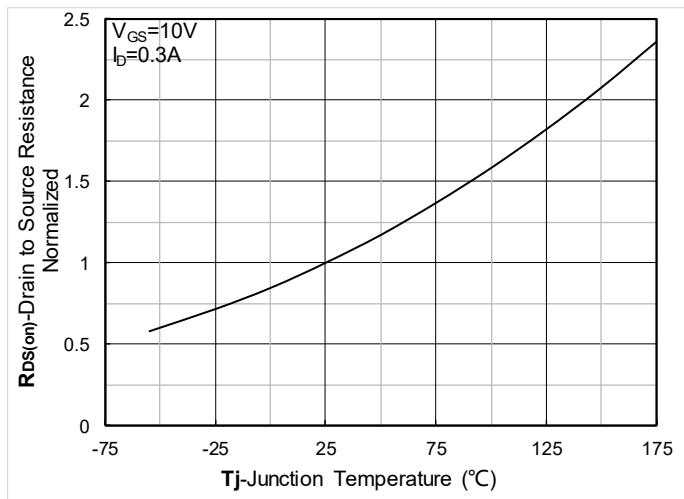


Figure 6. Normalized On-Resistance



2N7002DWKFHQ

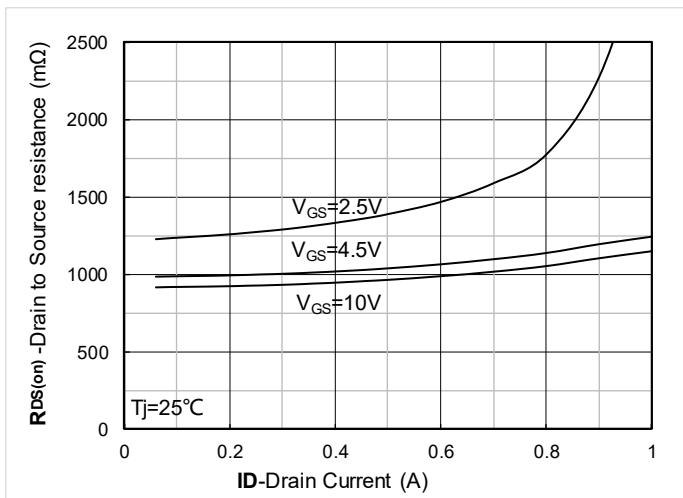


Figure 7. $R_{DS(on)}$ vs. Drain Current; typical values

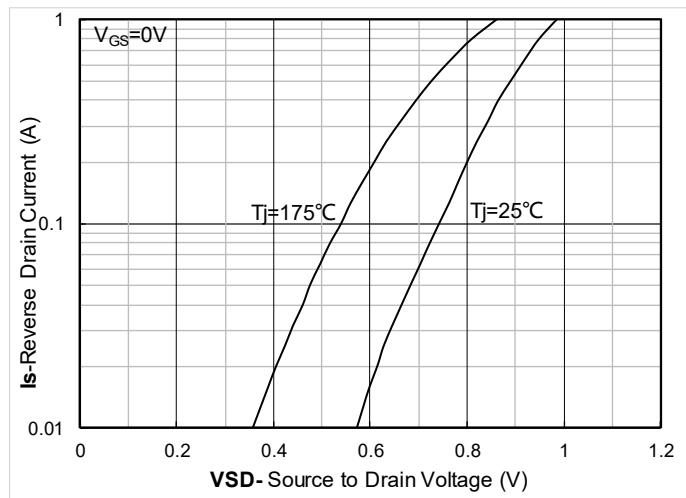


Figure 8. Forward characteristics of reverse diode; typical values

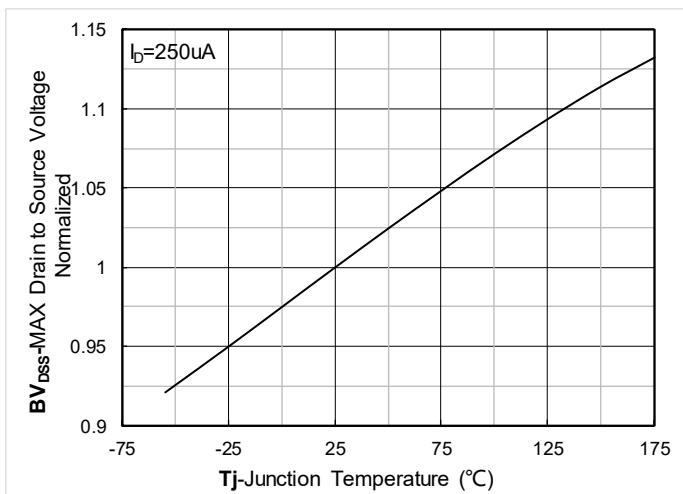


Figure 9. Normalized breakdown voltage

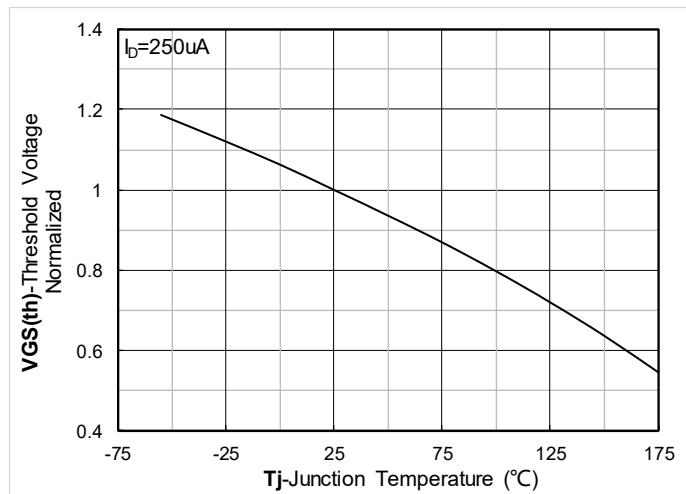


Figure 10. Normalized Threshold voltage

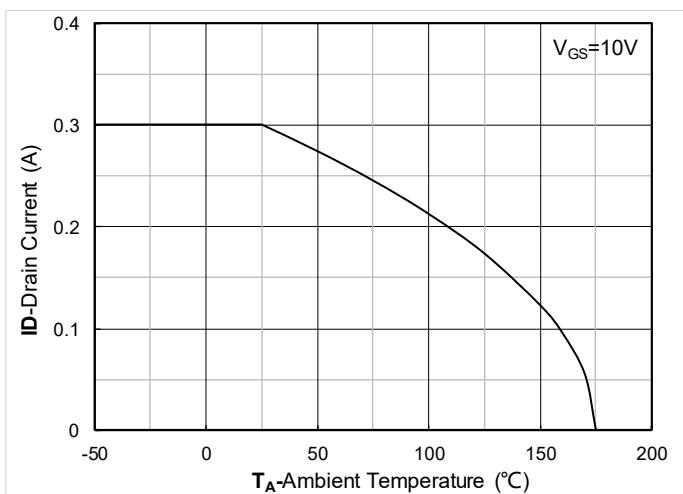


Figure 11. Current dissipation

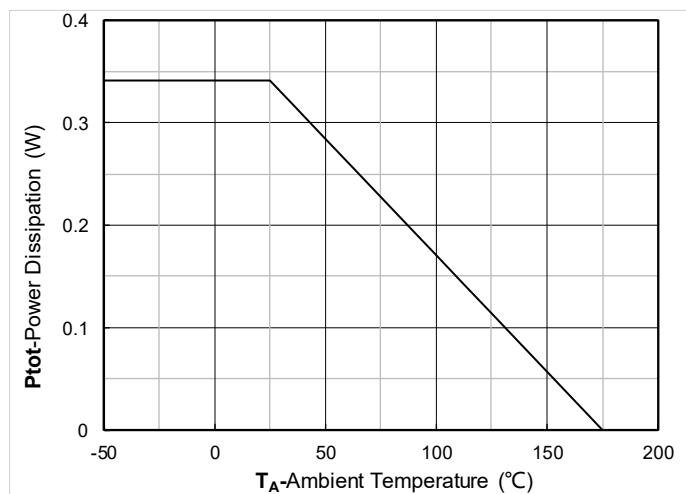


Figure 12. Power dissipation



2N7002DWKFHQ

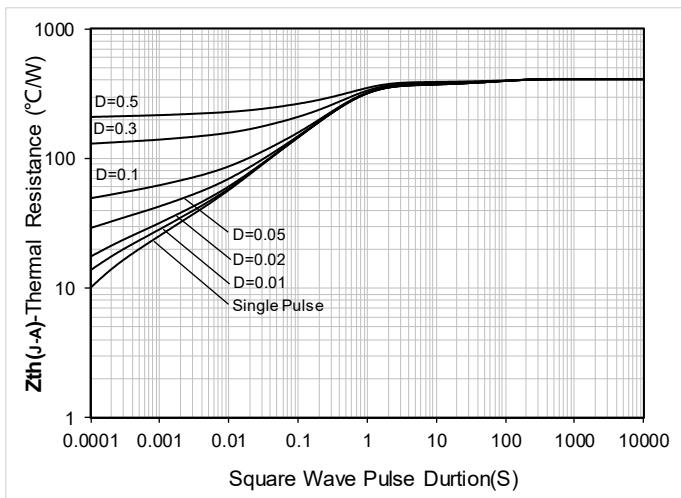


Figure 13. Maximum Transient Thermal Impedance

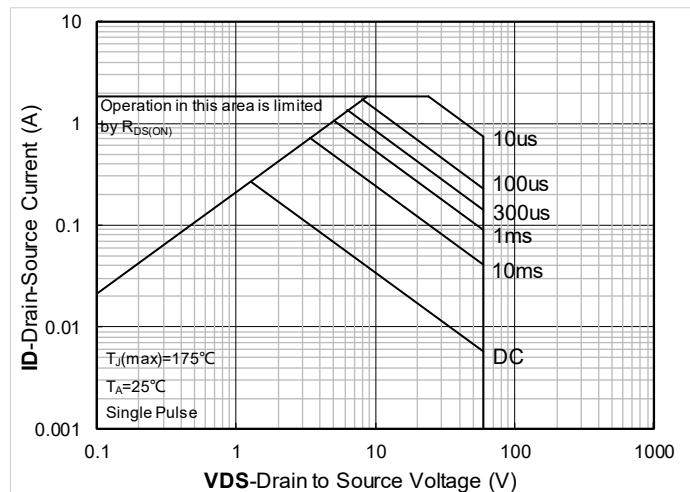


Figure 14. Safe Operation Area

■ Test Circuits & Waveforms

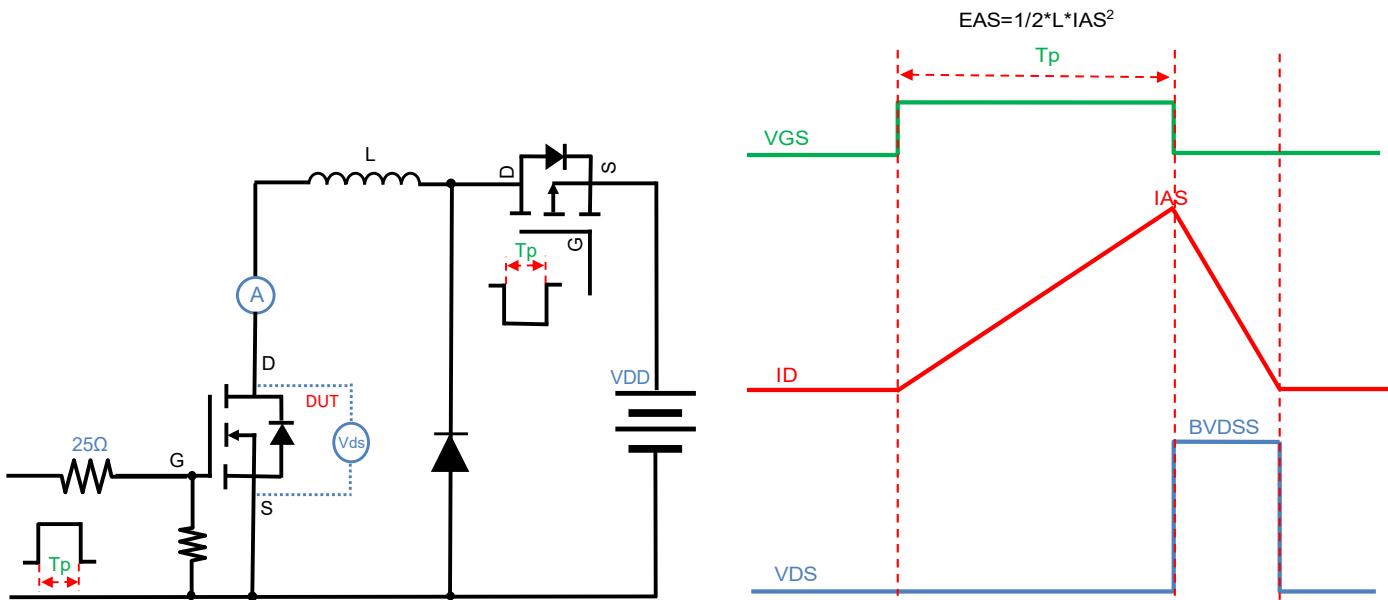


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

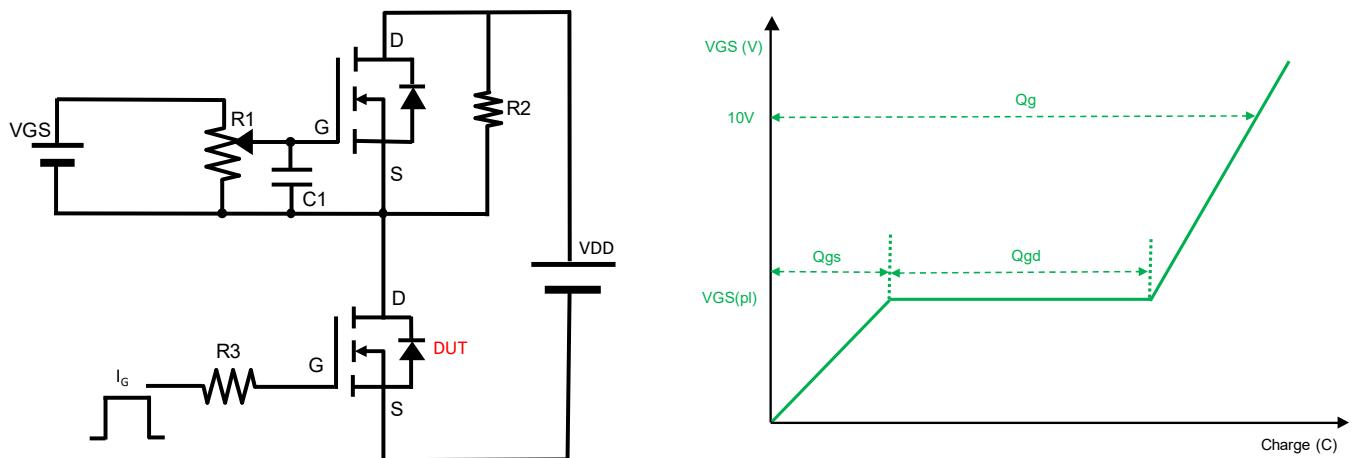


Figure B. Gate Charge Test Circuit & Waveform

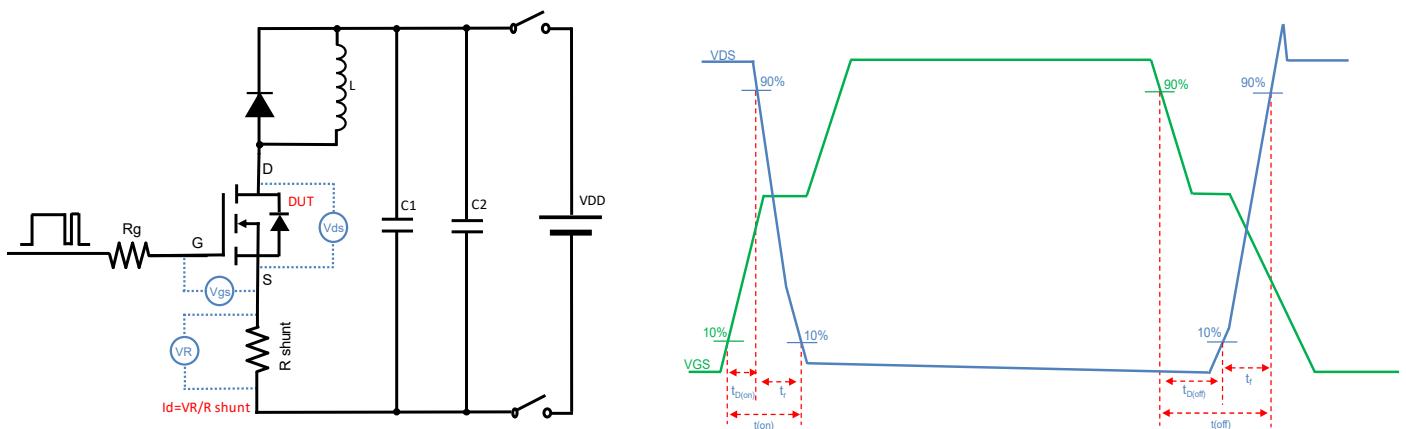


Figure C. Resistive Switching Test Circuit & Waveform

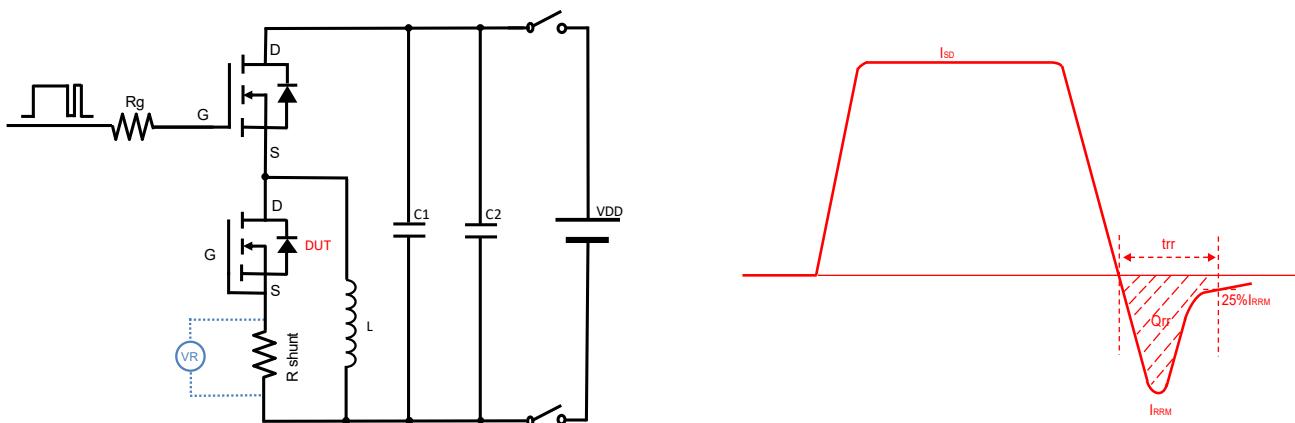
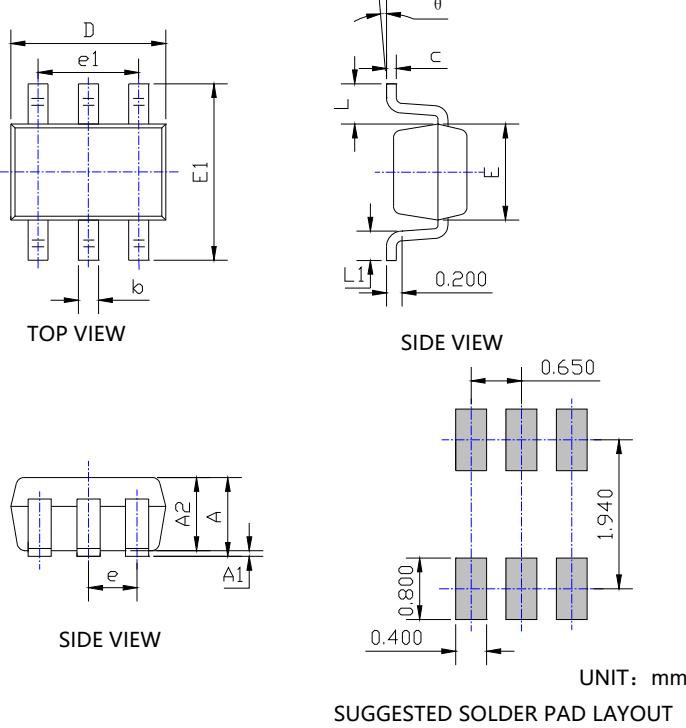


Figure D. Diode Recovery Test Circuit & Waveform



■ SOT-363 Package information



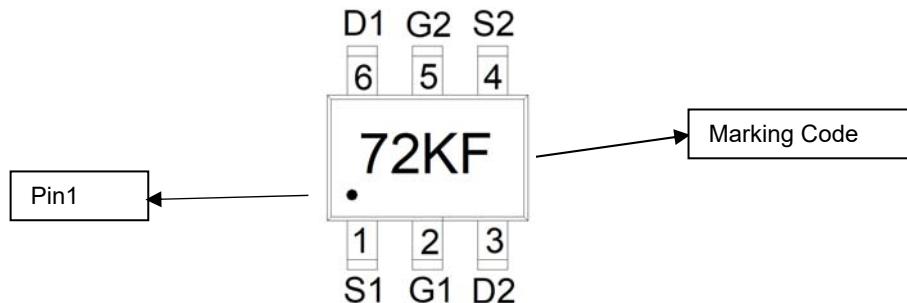
SYMBOL	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.035	0.043	0.900	1.100
A1	0.000	0.004	0.000	0.100
A2	0.035	0.039	0.900	1.000
b	0.006	0.014	0.150	0.350
c	0.004	0.010	0.100	0.250
D	0.071	0.087	1.800	2.200
E	0.045	0.053	1.150	1.350
E1	0.085	0.096	2.150	2.450
e	0.026TYP		0.650TYP	
e1	0.047	0.055	1.200	1.400
L	0.021REF		0.525REF	
L1	0.010	0.018	0.260	0.460
theta	0°	8°	0°	8°

NOTE:

- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



■ Marking Information



Note:

1. All marking is at middle of the product body
2. All marking is in laser printing
3. 72KF is Marking Code
4. Body color: Black



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